



AO8806

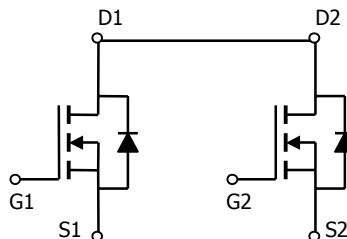
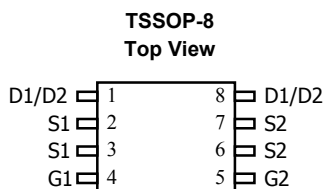
Common-Drain Dual N-Channel Enhancement Mode Field Effect Transistor

General Description

The AO8806 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 1.8V. This device is suitable for use as a uni-directional or bi-directional load switch, facilitated by its common-drain configuration.

Features

V_{DS} (V) = 20V
 I_D = 6 A
 $R_{DS(ON)} < 25m\Omega$ ($V_{GS} = 4.5V$)
 $R_{DS(ON)} < 30m\Omega$ ($V_{GS} = 2.5V$)
 $R_{DS(ON)} < 40m\Omega$ ($V_{GS} = 1.8V$)



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 8	V
Continuous Drain Current ^A	I_D	6.4	A
	I_D	5.4	A
Pulsed Drain Current ^B	I_{DM}	30	A
Power Dissipation ^A	P_D	1.5	W
	P_D	1.08	W
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	64	83	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	89	120	$^\circ\text{C/W}$
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	53	70	$^\circ\text{C/W}$

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	20			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =16V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±8V			100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} I _D =250μA	0.4	0.6	1	V
I _{D(ON)}	On state drain current	V _{GS} =4.5V, V _{DS} =5V	30			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =4.5V, I _D =6A T _J =125°C		19.3 27.6	25 35	mΩ
		V _{GS} =2.5V, I _D =5A		24	30	
		V _{GS} =1.8V, I _D =4A		30.5	40	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =5A	15	23		S
V _{SD}	Diode Forward Voltage	I _S =1A,V _{GS} =0V		0.76	1	V
I _S	Maximum Body-Diode Continuous Current				2.5	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =10V, f=1MHz		940		pF
C _{oss}	Output Capacitance			157		pF
C _{rss}	Reverse Transfer Capacitance			133		pF
SWITCHING PARAMETERS						
Q _g	Total Gate Charge	V _{GS} =4.5V, V _{DS} =10V, I _D =6A		15		nC
Q _{gs}	Gate Source Charge			1		nC
Q _{gd}	Gate Drain Charge			4		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =5V, V _{DS} =10V, R _L =1.8Ω, R _{GEN} =6Ω		6.5		ns
t _r	Turn-On Rise Time			9		ns
t _{D(off)}	Turn-Off DelayTime			56.5		ns
t _f	Turn-Off Fall Time			13.2		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =6A, dI/dt=100A/μs		22.4		ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =6A, dI/dt=100A/μs		8.4		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The value in any a given application depends on the user's specific board design. The current rating is based on the $t \leq 10\text{s}$ thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

D: The static characteristics in Figures 1 to 6,12,14 are obtained using 80 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The SOA curve provides a single pulse rating.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

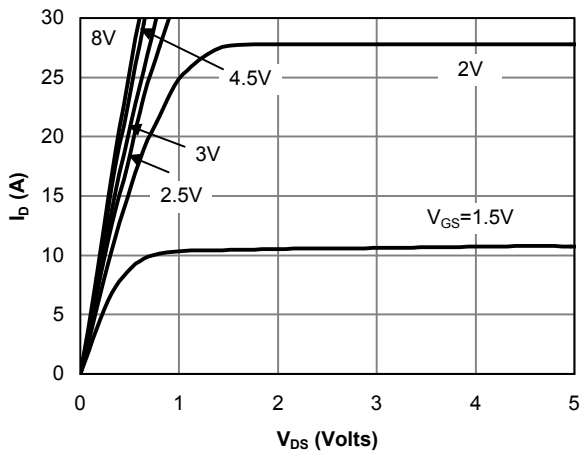


Fig 1: On-Region Characteristics

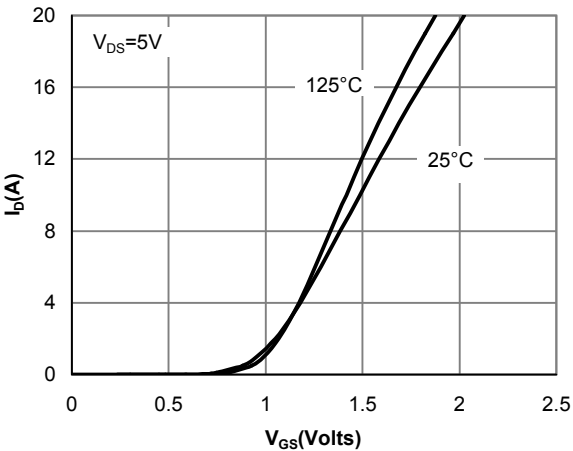


Figure 2: Transfer Characteristics

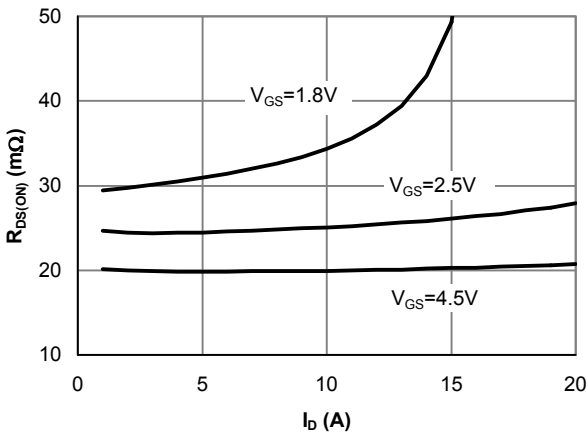


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

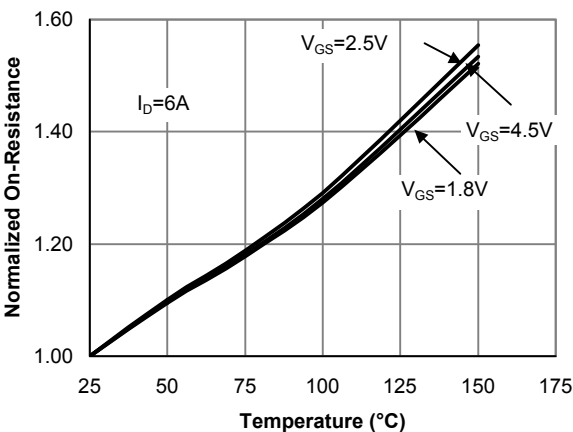


Figure 4: On-Resistance vs. Junction Temperature

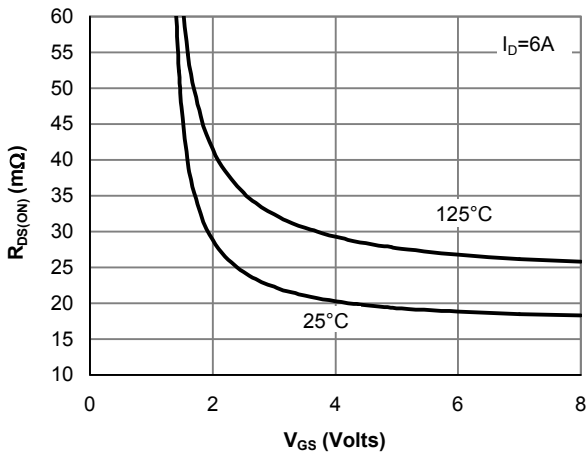


Figure 5: On-Resistance vs. Gate-Source Voltage

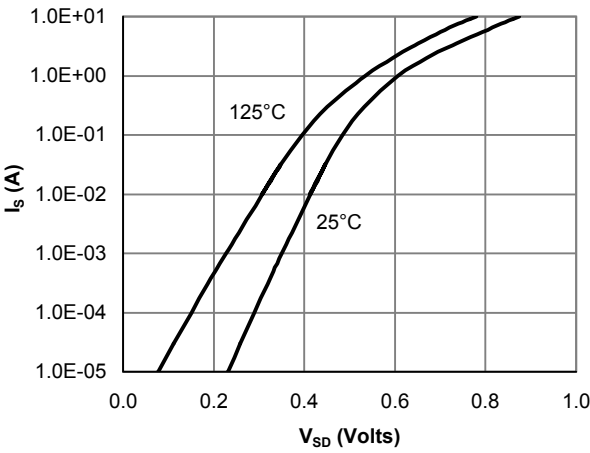


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

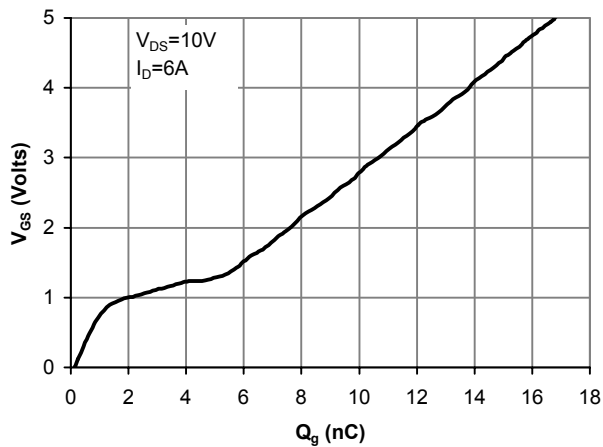


Figure 7: Gate-Charge Characteristics

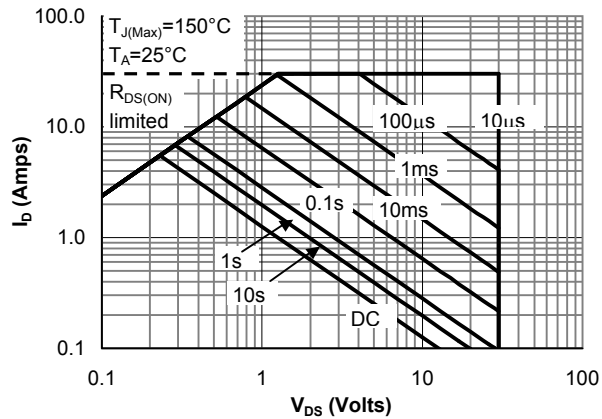
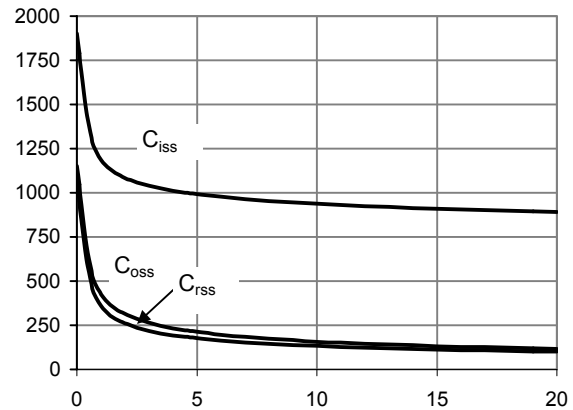


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

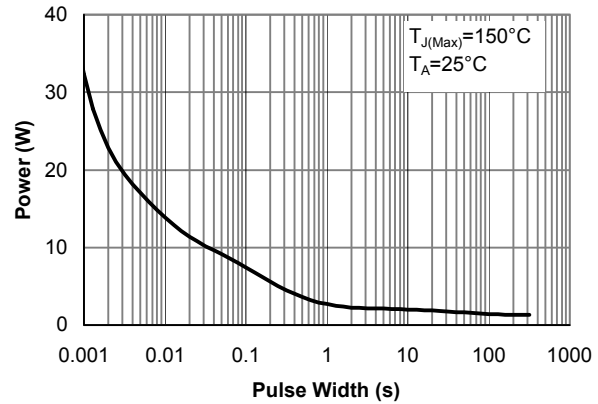


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

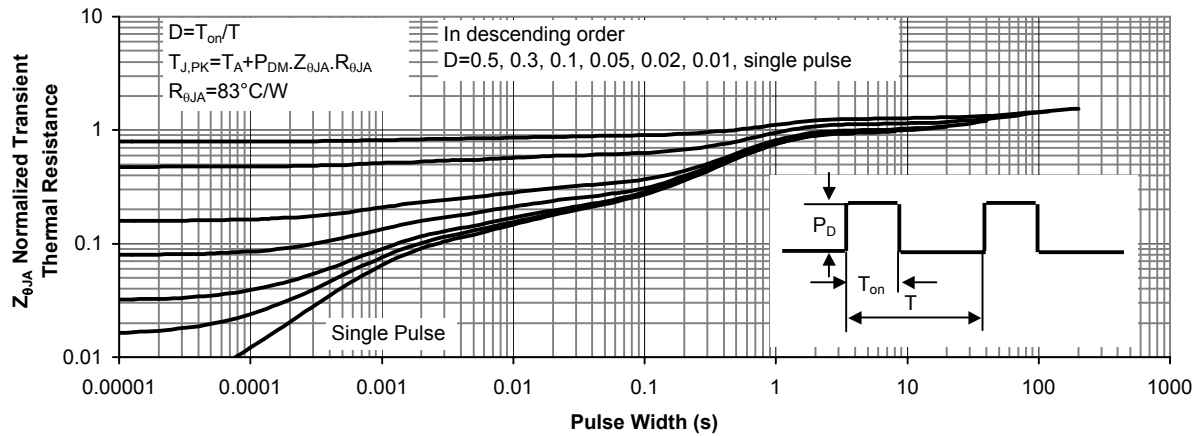


Figure 11: Normalized Maximum Transient Thermal Impedance